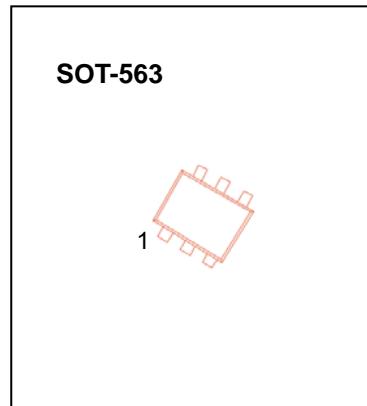


General purpose transistors (dual digital transistors)

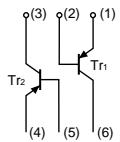


FEATURES

- Two 2SA1037AK chips in a package
- Mounting possible with SOT-563 automatic mounting machines
- Transistor elements are independent, eliminating interference

Marking: T1

Equivalent circuit



Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_c	Collector Current	-150	mA
P_c	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12\text{V}, I_C=-2\text{mA}, f=100\text{MHz}$		140		MHz
Output capacitance	C_{ob}	$V_{CB}=-12\text{V}, I_E=0, f=1\text{MHz}$			5	pF